

Supplementary Materials: Comparison of Vibration-Assisted Scratch Characteristics of SiC Polytypes (3C-, 4H- and 6H-SiC)

Wuqing Lin ^{1,2,3}, Zhongwei Hu ^{1,2,*}, Yue Chen ^{1,2}, Yuqiang Zhang ^{1,2}, Yiqing Yu ², Xipeng Xu ^{1,2} and Jie Zhang ³

¹ Institute of Manufacturing Engineering, Huaqiao University, Xiamen 361021, China; vince_lin@sanan-ic.com (W.L.); chen Yue@stu.hqu.edu.cn (Y.C.); 21011080019@stu.hqu.edu.cn (Y.Z.); xpxu@hqu.edu.cn (X.X.)

² Institute of Mechanical Engineering and Automation, Huaqiao University, Xiamen 361021, China; yyqing@hqu.edu.cn

³ Hunan Sanan Semiconductor Co., Ltd., Changsha 410000, China; jack_zhang@sanan-ic.com

* Correspondence: huzhongwei@hqu.edu.cn

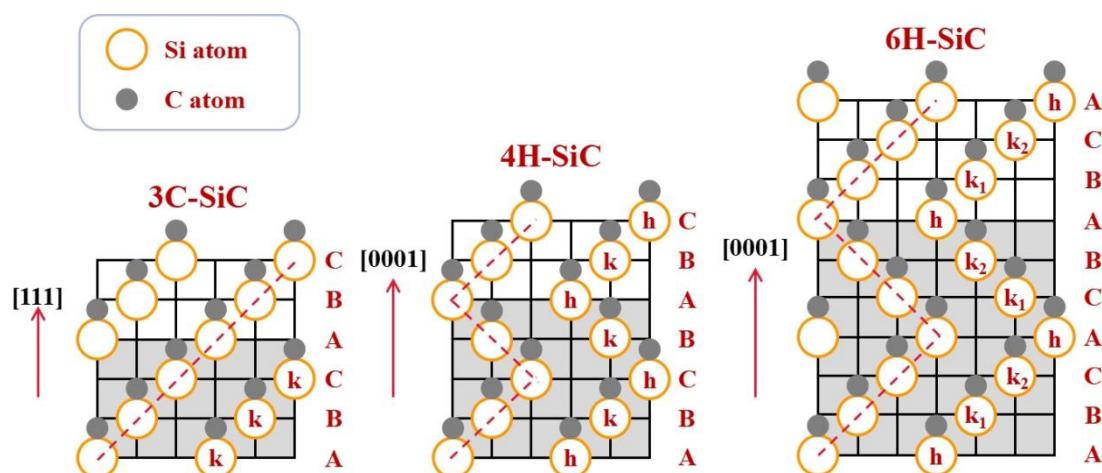


Figure S1. Schematic diagram of atomic arrangement of SiC polytypes (3C-, 4H- and 6H-SiC) [15], "h" and "k" represent the sites of hexagonal and cubic.

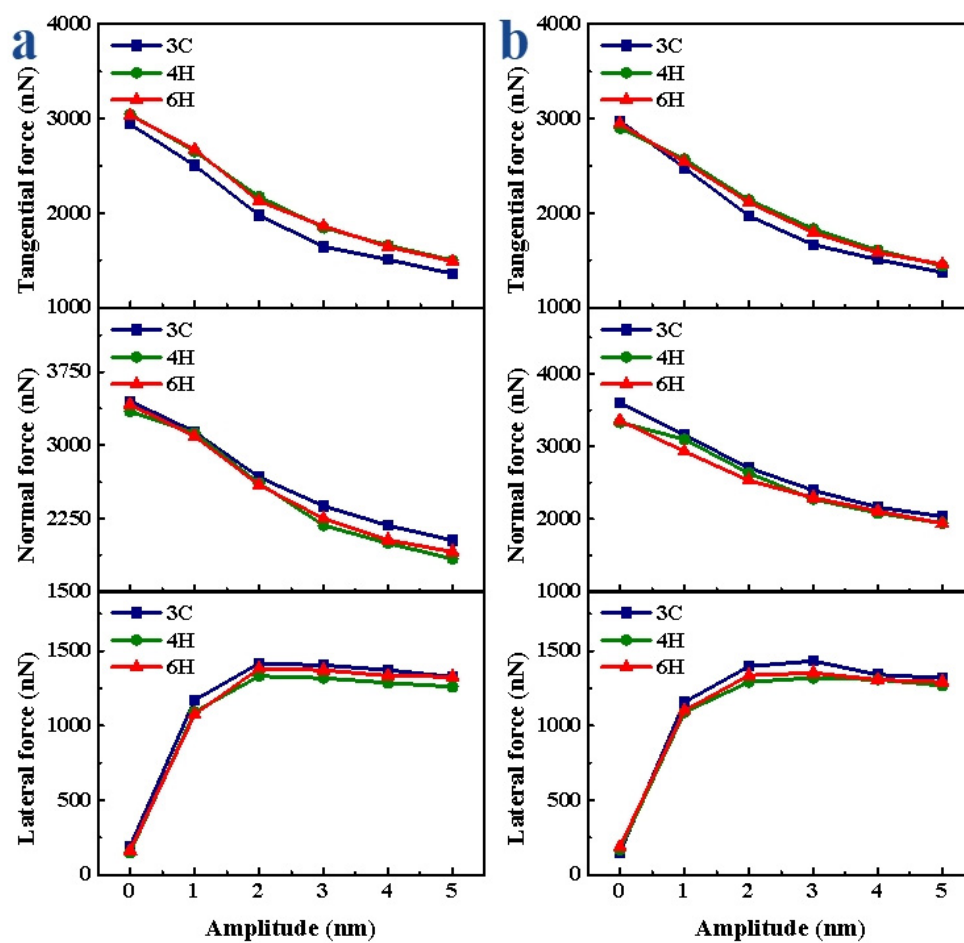


Figure S2. Variation of scratch force of SiC polytypes with different amplitudes: (a) Si-face and (b) C-face of SiC.

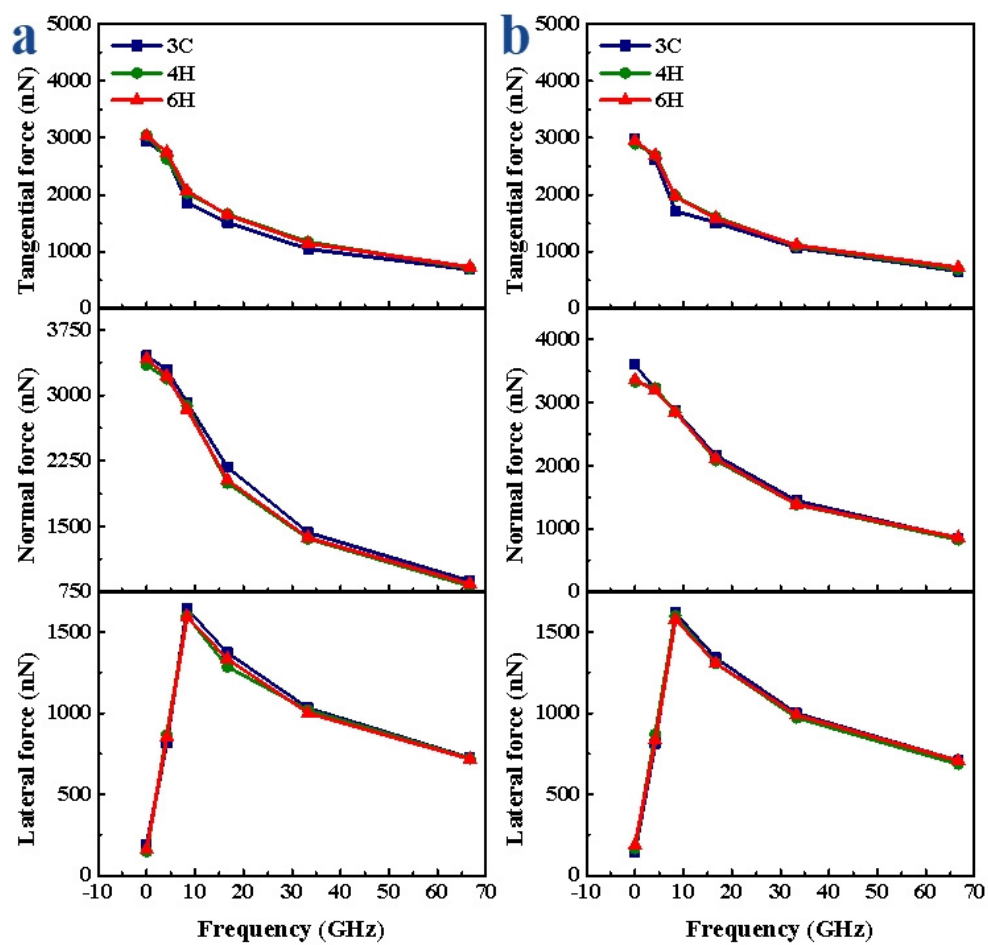


Figure S3. Variation of scratch force of SiC polytypes with different frequencies: (a) Si-face and (b) C-face of SiC.

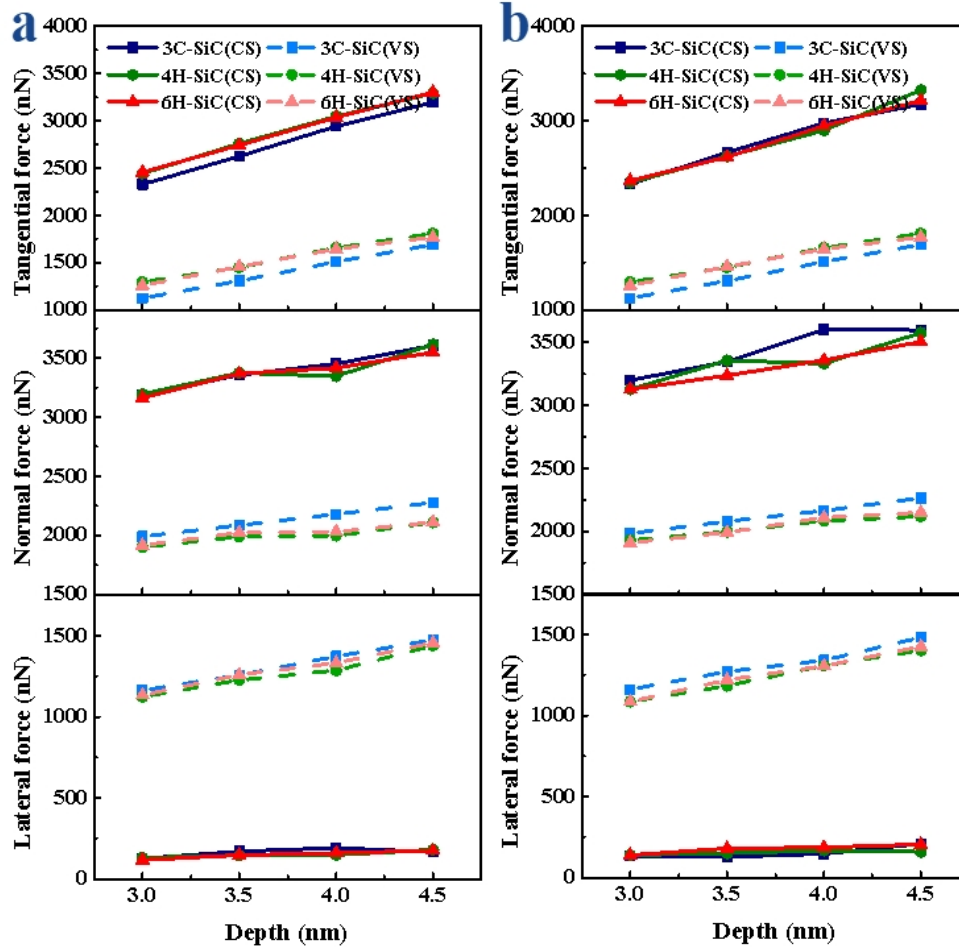


Figure S4. Variation of scratch force of SiC polytypes with different depths: (a) Si-face and (b) C-face of SiC.

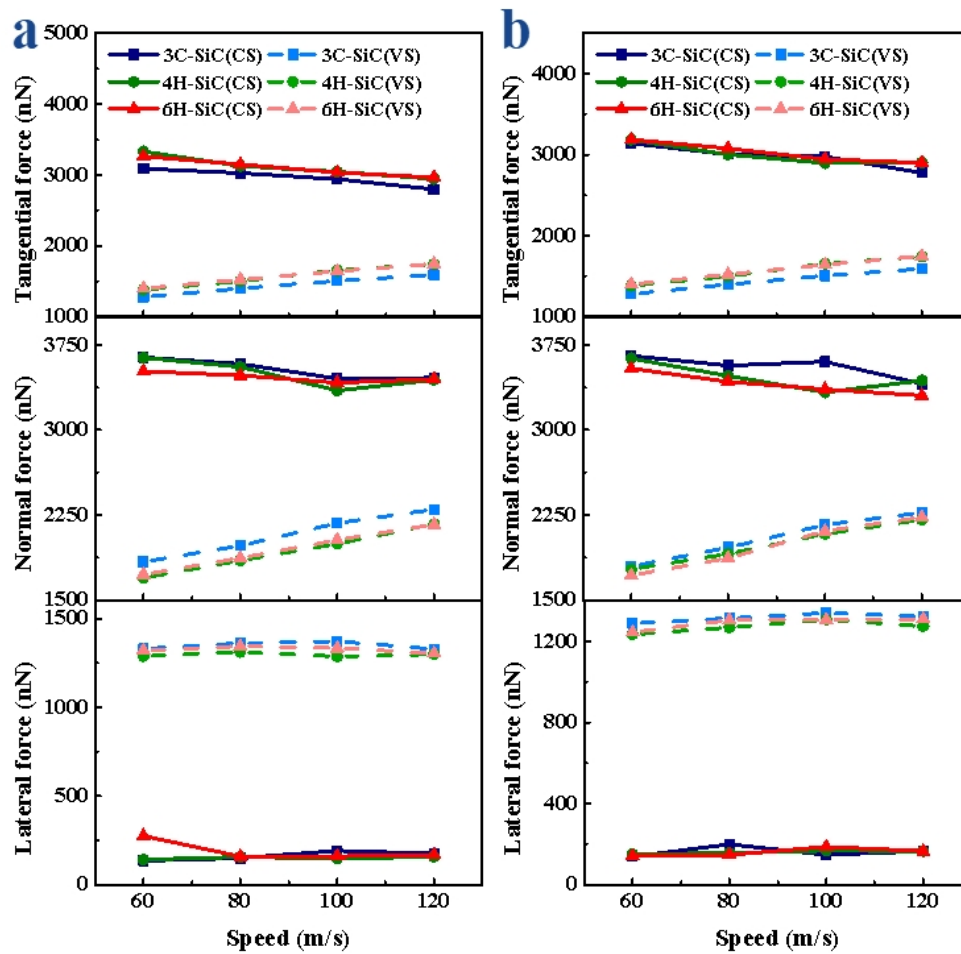


Figure S5. Variation of scratch force of SiC polytypes with different speeds: (a) Si-face and (b) C-face of SiC.